NEW PRODUCT

DMP6050SFG

60V P-CHANNEL ENHANCEMENT MODE MOSFET
POWERDI®

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max T_A = +25°C
-60V	50mΩ @ V_{GS} = -10V	-4.8A
	70mΩ @ V_{GS} = -4.5V	-4.1A

Features and Benefits

- Low $R_{DS(ON)}$ – Ensures On State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description and Applications

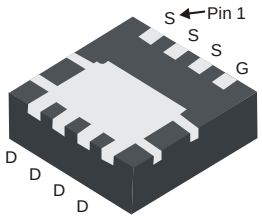
This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

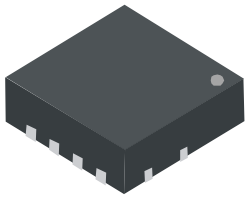
Mechanical Data

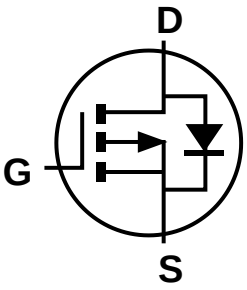
- Case: POWERDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.072 grams (Approximate)

POWERDI®3333-8



Bottom View


Top View



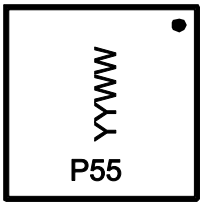
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP6050SFG-7	POWERDI®3333-8	2000/Tape & Reel
DMP6050SFG-13	POWERDI®3333-8	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



P55= Product Type Marking Code
YYWW = Date Code Marking
YY = Last Digit of Year (ex: 14 = 2014)
WW = Week Code (01 to 53)

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Maximum Ratings @T_A = +25°C, unless otherwise specified.

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = -10V	Steady State	T_A = +25°C T_A = +70°C	I_D	-4.8 -3.9	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	-6.0 -4.8	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	-32	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	-2.8	A
Avalanche Current (Note 7) L = 0.1mH			I_{AS}	-24.8	A
Repetitive Avalanche Energy (Note 7) L = 0.1mH			E_{AS}	30.8	mJ

Thermal Characteristics @T_A = +25°C, unless otherwise specified.

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	1.1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	118	°C/W
	t<10s		78	
Total Power Dissipation (Note 6)		P_D	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	71	°C/W
	t<10s		46	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	6.7	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = +25°C, unless otherwise specified.

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-60	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1	µA	V_{DS} = -60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1.0	—	-3.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	36	50	mΩ	V_{GS} = -10V, I_D = -5A
		—	47	70		V_{GS} = -4.5V, I_D = -4A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.2	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	1293	—	pF	V_{DS} = -30V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	86.3	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	64.7	—	pF	
Gate Resistance	R_g	—	12	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	11.9	—	nC	V_{DS} = -30V, I_D = -5A
Total Gate Charge (V_{GS} = -10V)	Q_g	—	24	—	nC	
Gate-Source Charge	Q_{gs}	—	3.6	—	nC	
Gate-Drain Charge	Q_{gd}	—	5.7	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	4.3	—	ns	V_{GS} = -10V, V_{DS} = -30V, R_G = 3Ω, I_D = -5A
Turn-On Rise Time	t_R	—	6.3	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	46.7	—	ns	
Turn-Off Fall Time	t_F	—	25.3	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	13.6	—	ns	I_F = -5A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	7.4	—	nC	I_F = -5A, di/dt = 100A/µs

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

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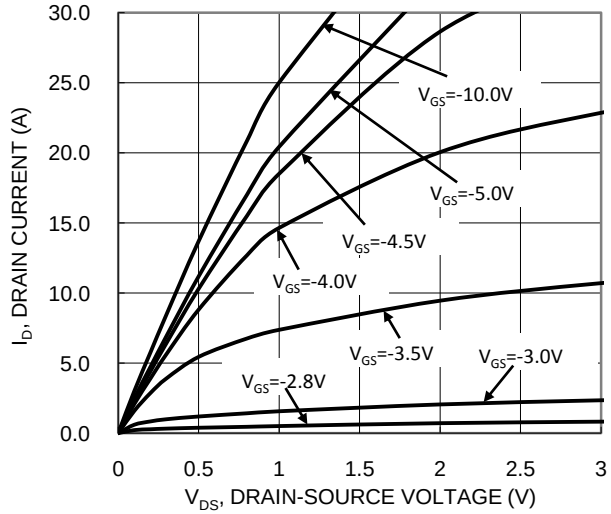

Figure 1 Typical Output Characteristic

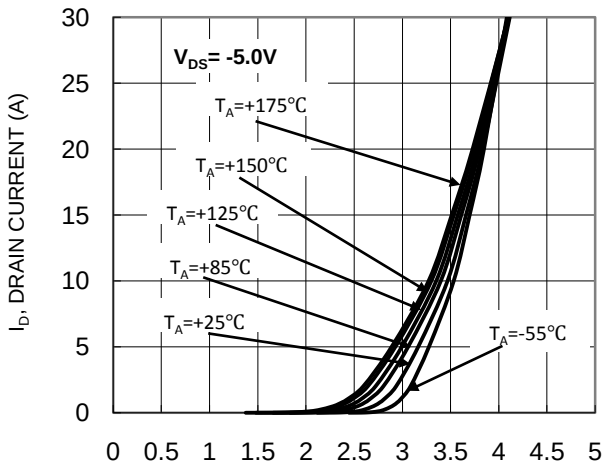

Figure 2 Typical Transfer Characteristic

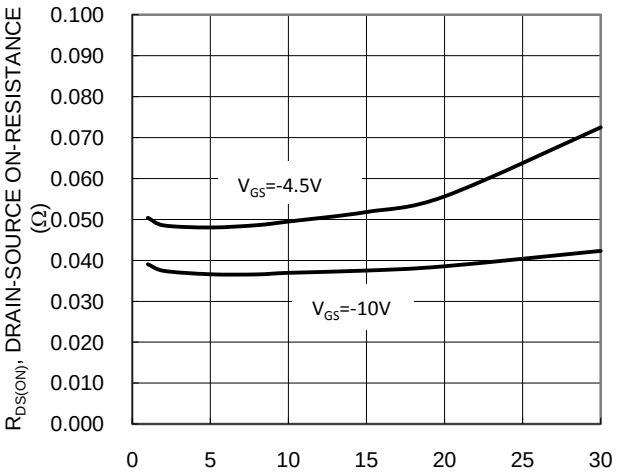

Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

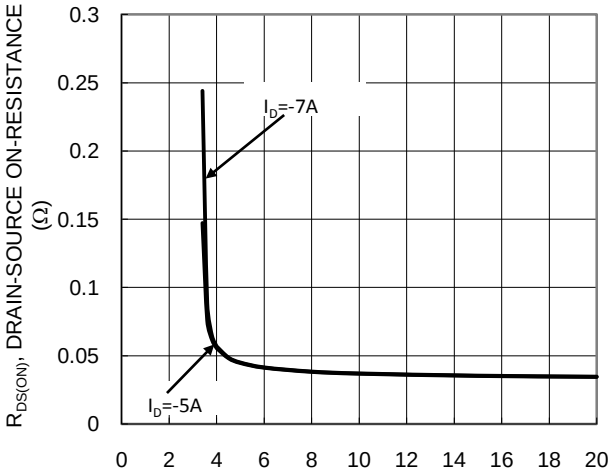

Figure 4 Typical Transfer Characteristic

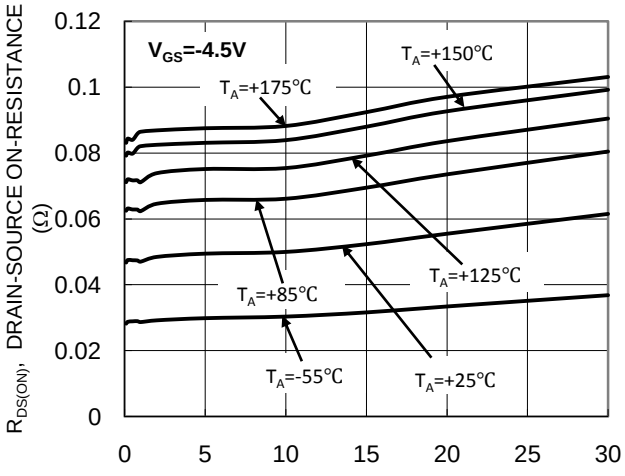

Figure 5 Typical On-Resistance vs. Drain Current and Temperature

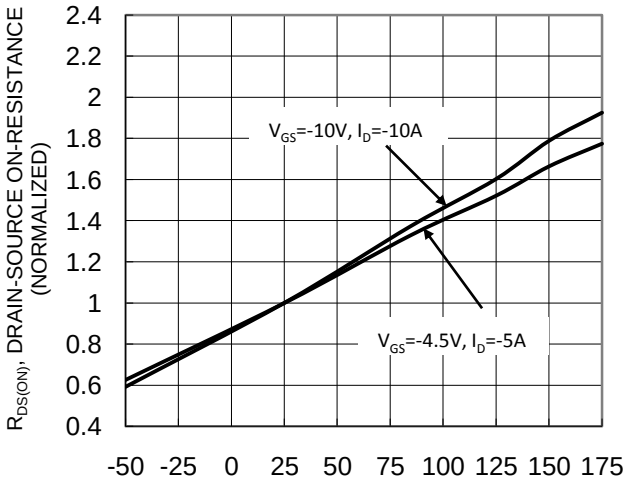

Figure 6 On-Resistance Variation with Temperature

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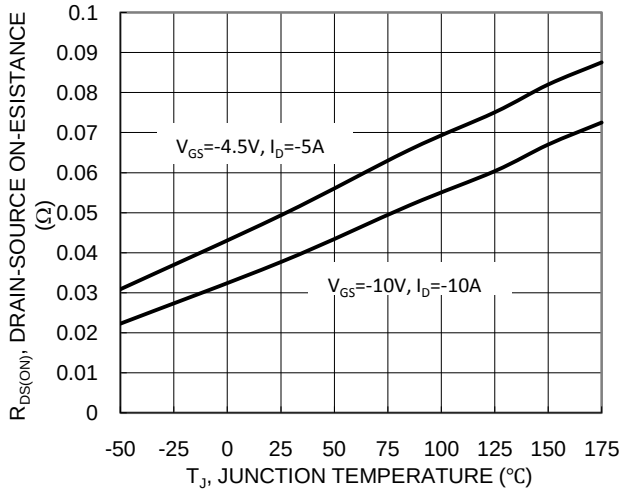

Figure 7 On-Resistance Variation with Temperature

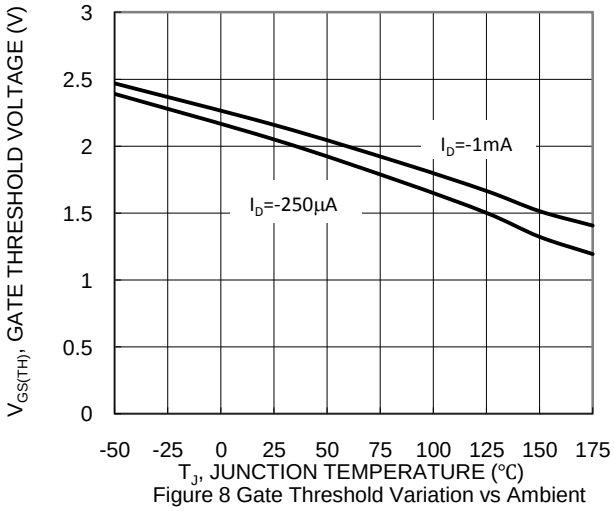

Figure 8 Gate Threshold Variation vs Ambient Temperature

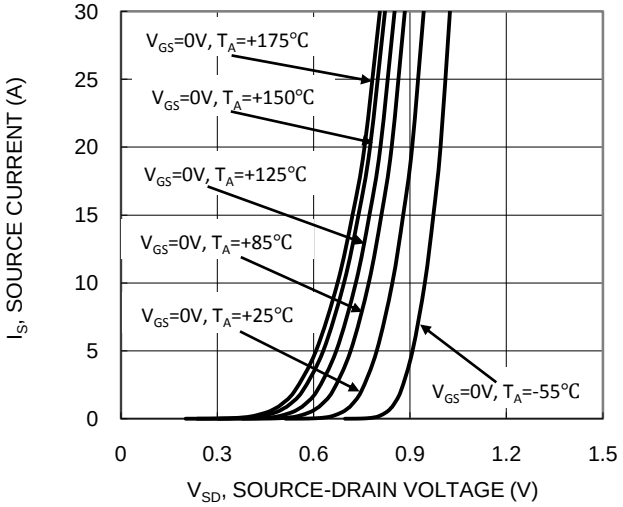

Figure 9 Diode Forward Voltage vs. Current

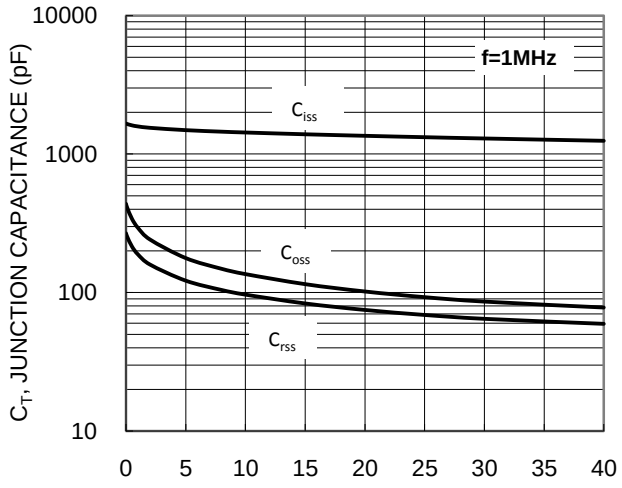

Figure 10 Typical Junction Capacitance

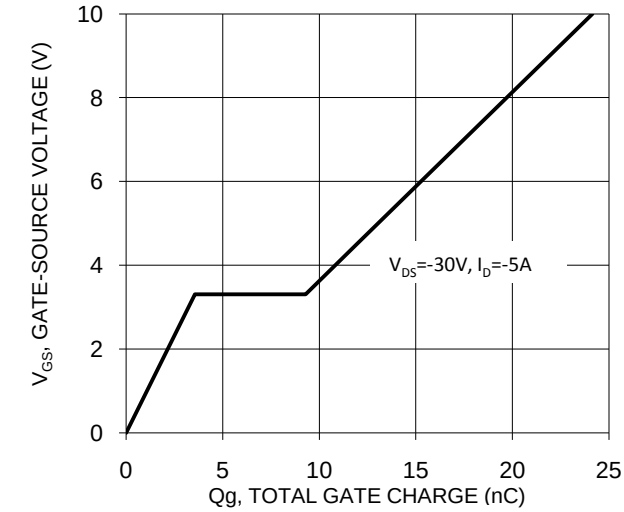

Figure 11 Gate Charge

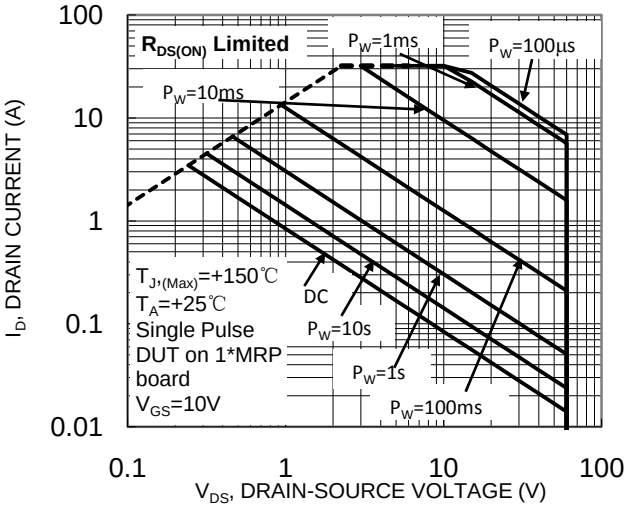

Figure 12 SOA, Safe Operation Area

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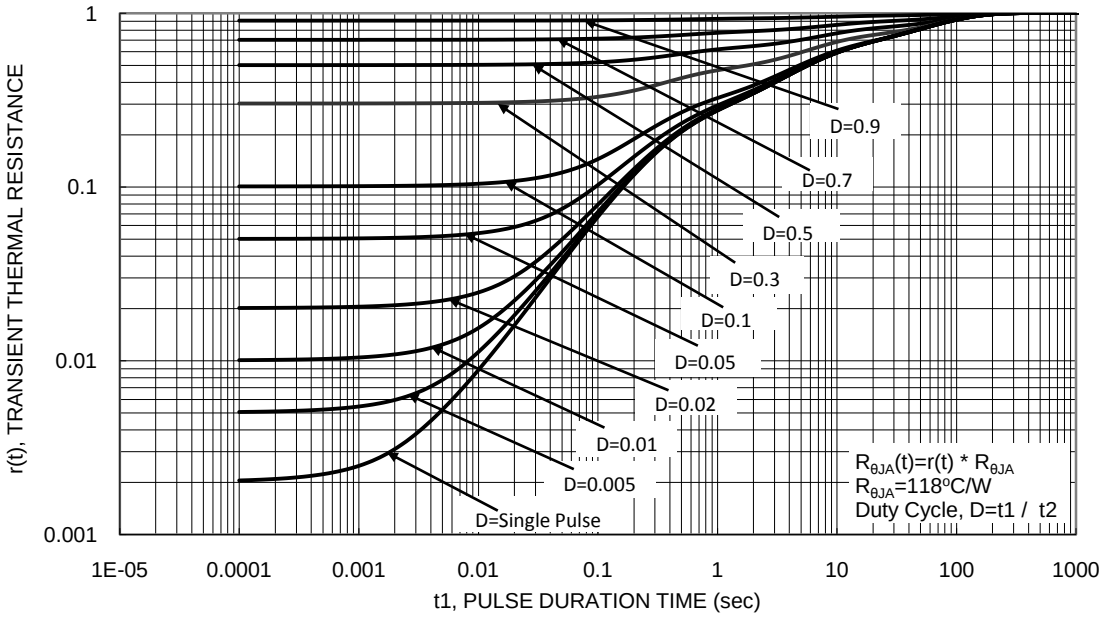
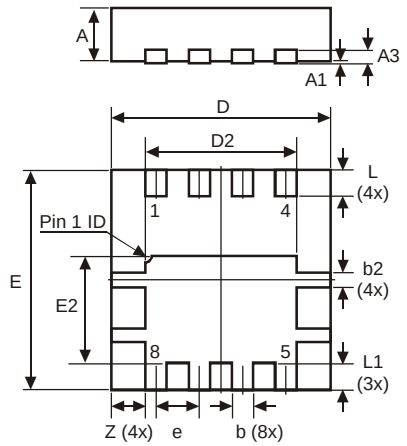


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

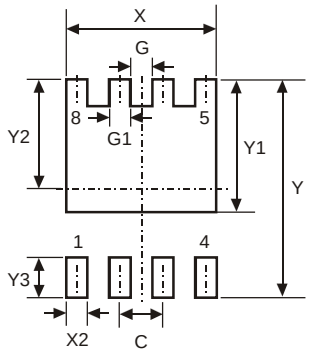
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI®3333-8			
Dim	**Min**	**Max**	**Typ**
D	3.25	3.35	3.30
E	3.25	3.35	3.30
D2	2.22	2.32	2.27
E2	1.56	1.66	1.61
A	0.75	0.85	0.80
A1	0	0.05	0.02
A3	–	–	0.203
b	0.27	0.37	0.32
b2	–	–	0.20
L	0.35	0.45	0.40
L1	–	–	0.39
e	–	–	0.65
Z	–	–	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.420
Y	3.700
Y1	2.250
Y2	1.850
Y3	0.700
X	2.370
X2	0.420

NEW PRODUCT

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